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SHEET 1 OF 1

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON 164P (U)	APPLICATION NO. 40121790 Unknown 10/618, 524
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Gilton, Terry L.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE April 10, 2002 July 14, 2003	GROUP 490 Unknown 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
Lee	5,761,115	6/2/1998	Kozicki, et al.				
Lee	5,896,312	4/20/1999	Kozicki, et al.				
Lee	5,914,893	6/22/1999	Kozicki, et al.				
Lee	6,084,796	07/04/00	Kozicki, et al.				

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Lee	WO 00/48196	08/17/00	WO				
Lee	WO 02/21542 A1	03/14/02	WO				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	P. Boolchand, et al., "Mobile Silver Ions and Glass Formation in Solid Electrolytes" <u>Nature</u> , Vol. 410, April 2001, pp. 1070-1073
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070902

EXAMINER <i>Rosie Mary Lee</i>	DATE CONSIDERED <i>2/12/04</i>
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON 184 (DU)	APPLICATION NO. 10/421,799 <i>Unknown</i> 10/618,824
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Gilton, Terry L.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE April 10, 2002 July 14, 2003	GROUP 2010 <i>Unknown</i> 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>Lee</i>		6,348,365	02/19/02	Moore, et al.			
<i>Lee</i>		6,418,040	07/09/02	Kozicki, et al.			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						

MSO-3448.DOC:afa
090602

EXAMINER <i>Lead Mary Lee</i>	DATE CONSIDERED <i>2/2/04</i>
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SHEET 1 OF 1

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.1648A1	APPLICATION NO. 10/421,790 <i>Unknown</i> 10/618,824
APPLICANT Gilton, Terry L.		FILING DATE April 10, 2002 <i>July 14, 2003</i>
GROUP 28TB <i>Unknown</i>		2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
<i>Lee</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	6,487,106	11/26/02	Kozicki				
	2002/0168820	11/14/02	Kozicki, et al.				
	2002/0190350	12/19/02	Kozicki, et al.				
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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

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042103

EXAMINER <i>Kevin Ming Lee</i>	DATE CONSIDERED <i>2/12/04</i>
<small>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</small>	



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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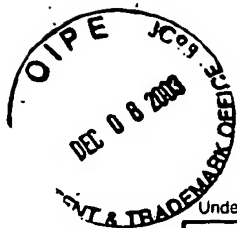
Complete if Known

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Art Unit	N/A 2823
Examiner Name	Not Yet Assigned H. Lee
Attorney Docket Number	M4065.1006/P1006-A

Sheet 1 of 12

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
✓	AA	2002/0000666	1/2002	Kozicki et al.	
*	AB	2002/0072188	6/2002	Gilton	
*	AC	2002/0106849	08/2002	Moore	
*	AD	2002/0123169	09/2002	Moore et al.	
*	AE	2002/0123170	09/2002	Moore et al.	
*	AF	2002/0123248	09/2002	Moore et al.	
*	AG	2002/0127886	09/2002	Moore et al.	
*	AH	2002/0132417	09/2002	Li	
*	AI	2002/0160551	10/2002	Harshfield	
*	AJ	2002/0163828	11/2002	Krieger et al.	
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*	AO	2003/0032254	02/2003	Gilton	
*	AP	2003/0038301	02/2003	Moore	
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*	AR	2003/0045049	03/2003	Campbell et al.	
*	AS	2003/0045054	03/2003	Campbell et al.	
*	AT	2003/0047765	03/2003	Campbell	
*	AU	2003/0047772	03/2003	Li	
*	AV	2003/0047773	03/2003	Li	
*	AW	2003/0049912	03/2003	Campbell et al.	
*	AX	2003/0068861	04/2003	Li	
*	AY	2003/0068862	04/2003	Li	
*	AZ	2003/0095426	05/2003	Hush et al.	
*	AA1	2003/0096497	05/2003	Moore et al.	
*	AB1	2003/0107105	06/2003	Kozicki	
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*	AM1	2003/0210564	11/2003	Kozicki et al.	
*	AN1	3,622,319	11/1971	Sharp	
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*	AP1	4,269,935	5/1981	Masters et al.	
*	AQ1	4,312,938	1/1982	Drexler, et al.	
✓	AR1	4,316,946	1/1982	Masters, t al.	



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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A-2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	2	of	12	Attorney Docket Number	M4065.1006/P1006-A

Lee	AS1	4,320,191	3/1982	Yoshikawa et al.	
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*	AU1	4,419,421	12/1983	Wichelhaus, et al.	
*	AV1	4,499,557	2/1985	Holmberg et al.	
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*	AX1	4,795,657	1/1989	Formigoni et al.	
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*	AE2	5,314,772	5/1994	Kozicki	
*	AF2	5,315,131	5/1994	Kishimoto et al.	
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PTO/SB/08A (10-01)

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			Application Number	10/618,824	
			Filing Date	July 14, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	N/A- 2823	
			Examiner Name	Not Yet Assigned H. Lee	
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-A

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code ² -Number ⁴ -Kind Code ³ (if known)					
	BA	JP-56126916		10/1981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		

Examiner Signature	<i>Heidi Mary Lee</i>	Date Considered	2/12/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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Substitute for form 1449B/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/618,824		
		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	<i>NA 2823</i>		
		Examiner Name	<i>Not Yet Assigned H. Lee</i>		
Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
<i>Lee</i>	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.		
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
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	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.		
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	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
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	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
	CS	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.		
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	CU	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.		
<i>Lee</i>	CV	Bernede, J.C. et al., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.		



PTO/SB/08B (10-01)

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U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	HA 2823
Examiner Name	Not Yet Assigned H. Lee
Attorney Docket Number	M4065.1006/P1006-A

Sheet	6	of	12
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✓	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.	
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✓	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
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✓	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
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		Examiner Name	Not Yet Assigned H. Lee		
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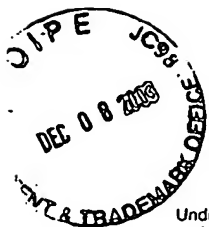
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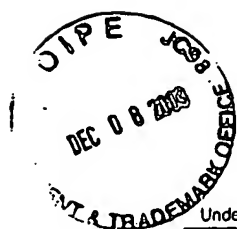
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				Application Number	10/618,824
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				Group Art Unit	NTA 2823
				Examiner Name	Not Yet Assigned H. Lee
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Sheet	12	of	12		

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Examiner Signature	<i>Hees Mary Lee</i>	Date Considered	<i>2/2/54</i>
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